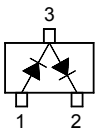
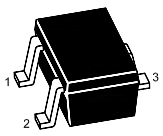
BAV199W

Silicon Epitaxial Planar Diode

Low leakage switching double diode

For low leakage current applications





SOT-323 Plastic Package

Marking Code: **JY**

Feature

- Very low leakage current
- Medium speed switching times
- Series pair configuration

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage		V_{RRM}	85	V
Continuous Reverse Voltage		V_R	85	V
Continuous Forward Current	Single Diode Double Diode	I_F	160 140	mA
Repetitive Peak Forward Current		I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current	at t = 1 µs at t = 1 ms at t = 1 s	I_{FSM}	4 1 0.5	A
Power Dissipation		P_d	250	mW
Thermal Resistance Junction to Ambient Air		$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range		T_j, T_{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at I_R = 100 µA	$V_{(BR)R}$	85	-	V
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50 mA at I_F = 150 mA	V_F	- - - -	0.9 1 1.1 1.25	V
Reverse Current at V_R = 75 V at V_R = 75 V, T_j = 150 °C	I_R I_R	- -	5 80	nA
Total Capacitance at V_R = 0, f = 1 MHz	C_T	-	2	pF
Reverse Recovery Time at I_F = I_R = 10 mA, I_{rr} = 0.1 X I_R, R_L = 100 Ω	t_{rr}	-	3	µs

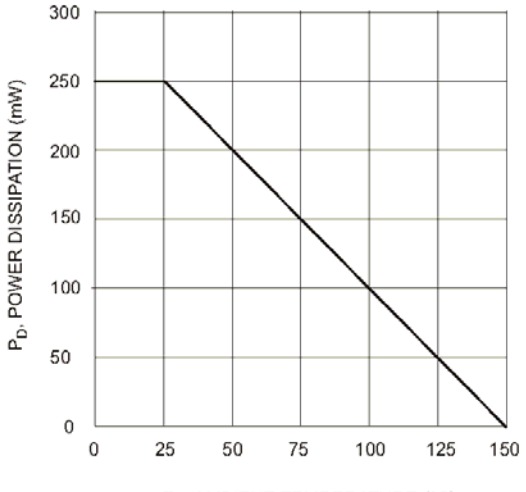


Fig. 1 Power Derating Curve

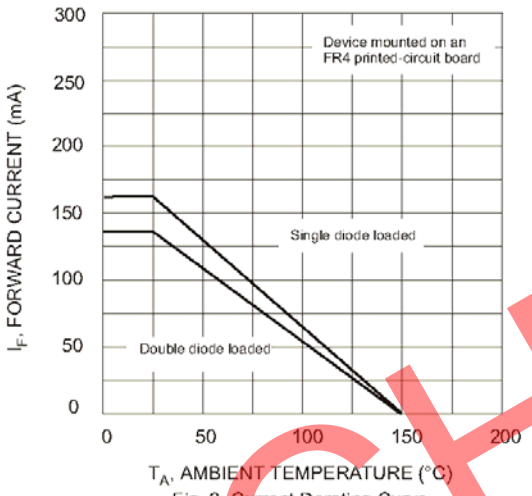


Fig. 2 Current Derating Curve

Fig. 3 Typical Forward Characteristics

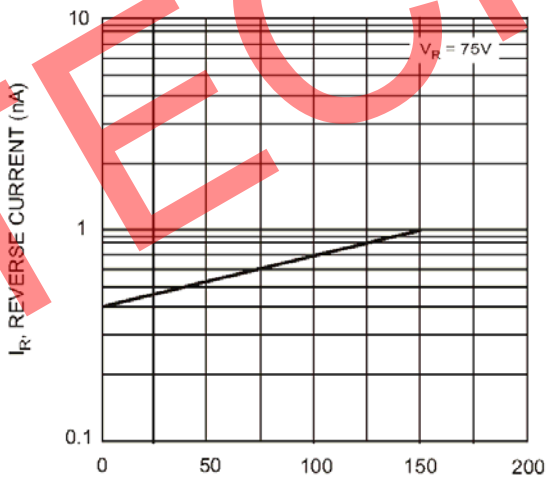


Fig. 4 Typical Reverse Characteristics